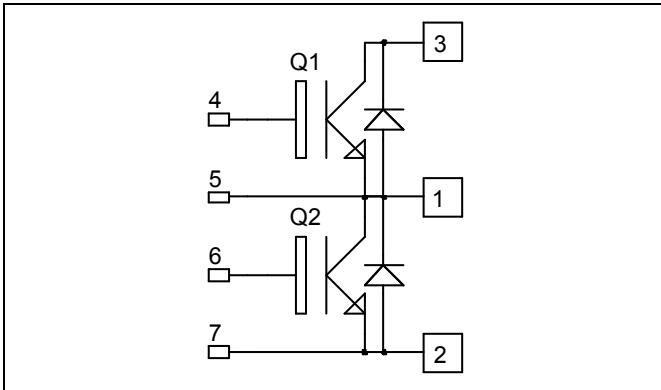


## Phase leg NPT IGBT Power Module

$V_{CES} = 1200V$   
 $I_C = 200A @ T_c = 80^\circ C$



### Application

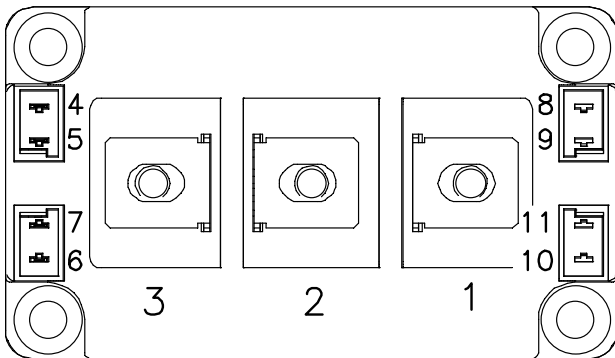
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Non Punch Through (NPT) FAST IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant



### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	1200	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ C$	300
		$T_C = 80^\circ C$	200
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ C$	400
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$	1400
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	400A@1150V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 1200\text{V}$			5	mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15\text{V}$ $I_C = 200\text{A}$	$T_j = 25^\circ\text{C}$	3.2	3.7	V
			$T_j = 125^\circ\text{C}$	3.9		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 8\text{mA}$	5.2	5.8	6.4	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			400	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0\text{V}, V_{CE} = 25\text{V}$		13		nF
$C_{res}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		1		
$Q_G$	Gate charge	$V_{GE} = \pm 15\text{V}, I_C = 200\text{A}$ $V_{CE} = 600\text{V}$		2.1		$\mu\text{C}$
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 200\text{A}$ $R_G = 4.7\Omega$		100		ns
$T_r$	Rise Time			60		
$T_{d(off)}$	Turn-off Delay Time			530		
$T_f$	Fall Time			30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ ) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 200\text{A}$ $R_G = 4.7\Omega$		110		ns
$T_r$	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			550		
$T_f$	Fall Time			40		
$E_{on}$	Turn On Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 200\text{A}$	$T_j = 125^\circ\text{C}$	19		mJ
$E_{off}$	Turn Off Energy	$R_G = 4.7\Omega$	$T_j = 125^\circ\text{C}$	15		
$I_{sc}$	Short Circuit data	$V_{GE} \leq 15\text{V}; V_{Bus} = 900\text{V}$ $t_b \leq 10\mu\text{s}; T_j = 125^\circ\text{C}$		1300		A

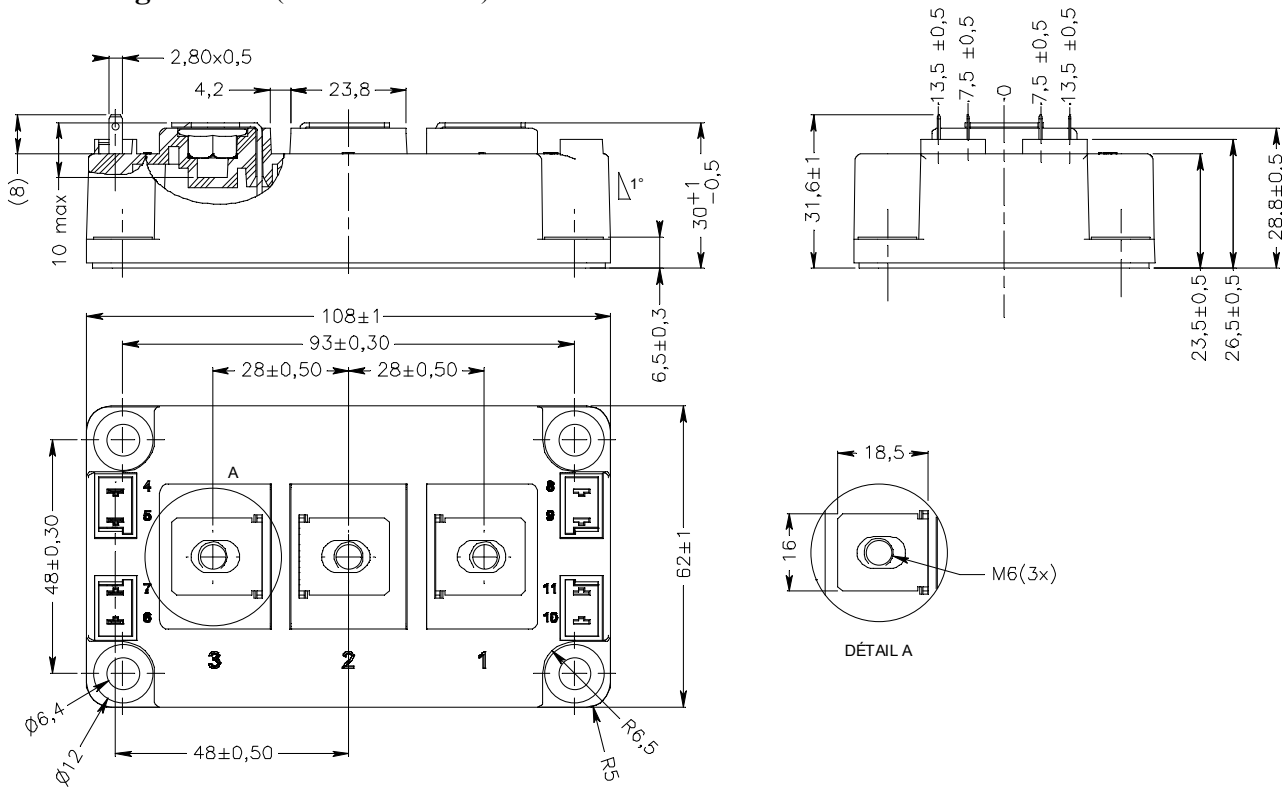
**Reverse diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1200			V
$I_{RRM}$	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$		750	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		1000	
$I_F$	DC Forward Current			200		A
$V_F$	Diode Forward Voltage	$I_F = 200\text{A}$	$T_j = 25^\circ\text{C}$	2.1		V
			$T_j = 125^\circ\text{C}$	1.9		
$t_{rr}$	Reverse Recovery Time	$I_F = 200\text{A}$ $V_R = 600\text{V}$ $di/dt = 3000\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	100		ns
			$T_j = 125^\circ\text{C}$	200		
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	14		$\mu\text{C}$
			$T_j = 125^\circ\text{C}$	40		
$E_{rr}$	Reverse Recovery Energy	$T_j = 25^\circ\text{C}$	5.2		mJ	
		$T_j = 125^\circ\text{C}$	11.2			

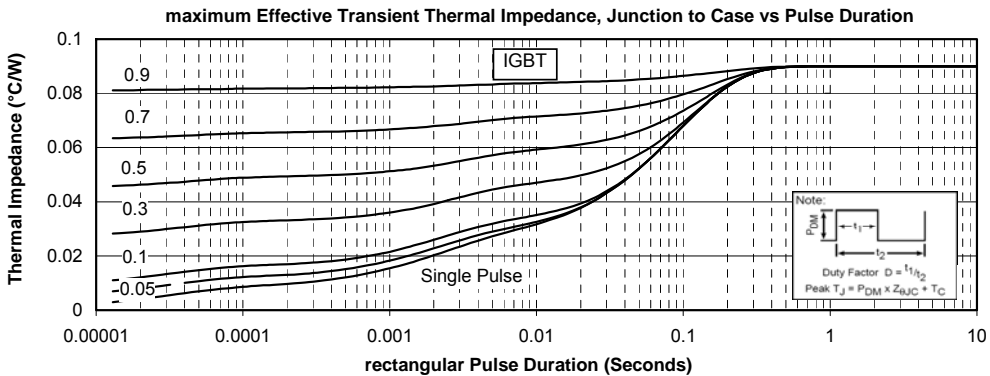
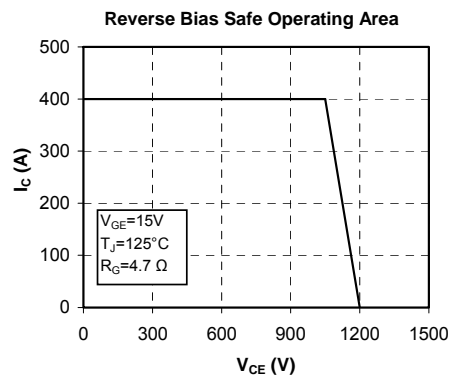
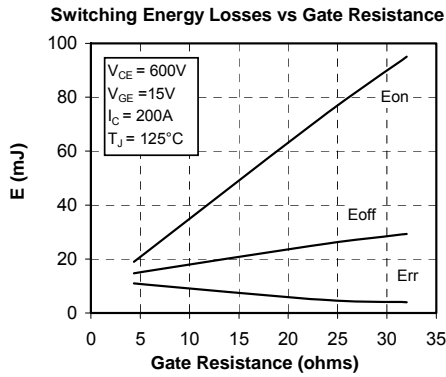
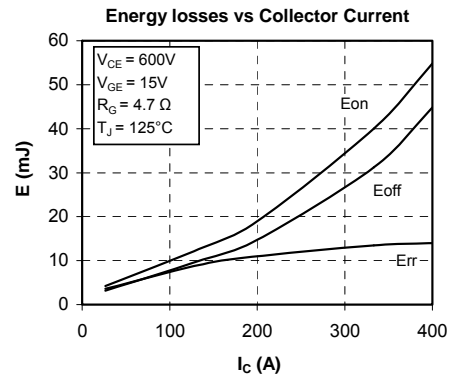
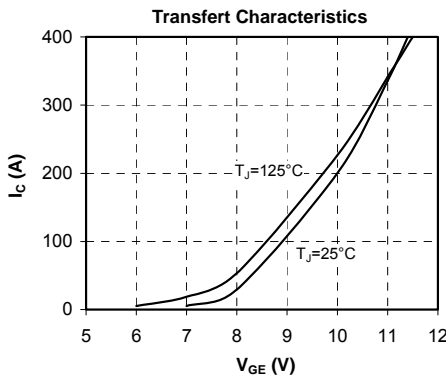
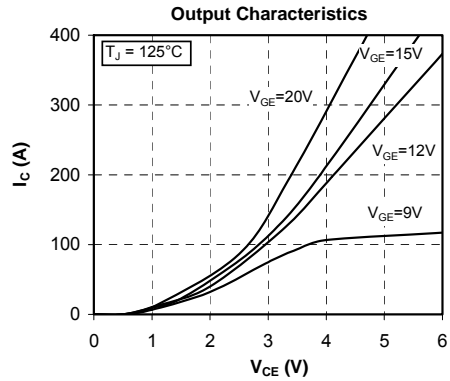
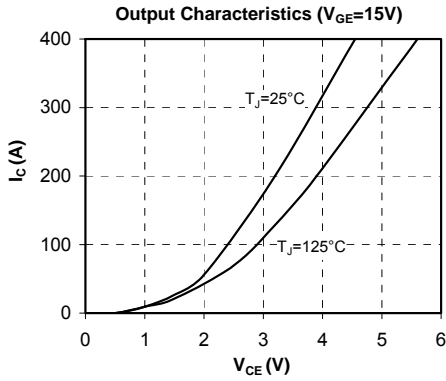
## Thermal and package characteristics

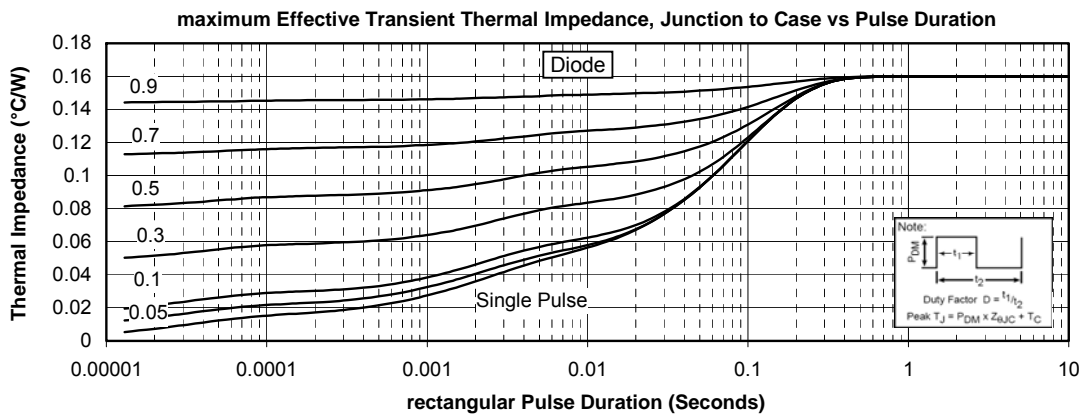
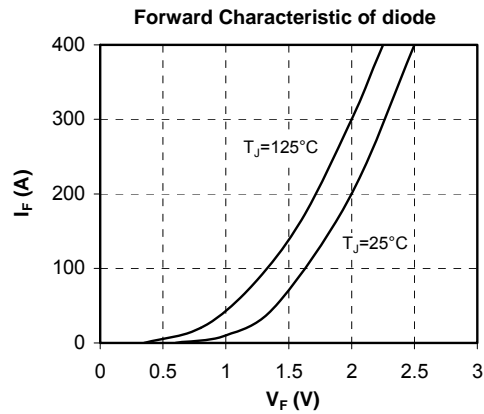
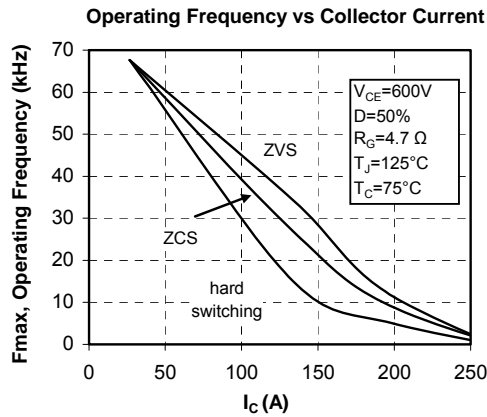
Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT		0.09	°C/W	
		Diode		0.16		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I <sub>isol</sub> <1mA, 50/60Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		125		
Torque	Mounting torque	For terminals	M6	3	5	N.m
		To Heatsink	M6	3	5	
Wt	Package Weight			350	g	

## D3 Package outline (dimensions in mm)



## Typical Performance Curve





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Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.